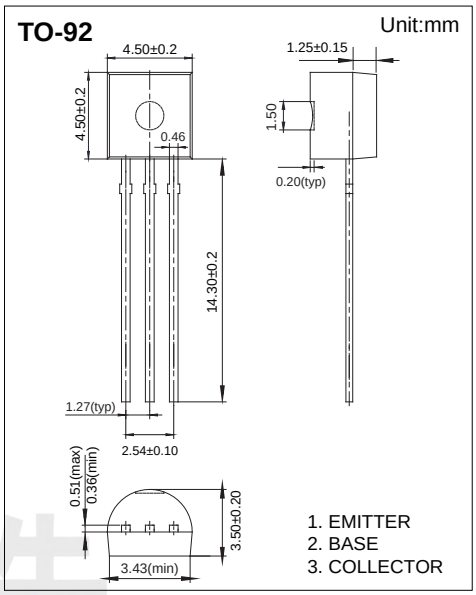
PNP Transistors

A92



■ Features

- ● High voltage
- ● Complementary to A42

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-310	V
Collector - Emitter Voltage	V_{CEO}	-305	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-200	mA
Collector Current -Pulsed	I_{CM}	-500	
Collector Power Dissipation	P_C	625	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	℃/mW
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	

PNP Transistors

A92

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V_{CBO}	I_C= -100 μA， I_E=0	-310			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA， I_B=0	-305			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μA， I_C=0	-5			
Collector cut-off current	I_{CBO}	V_{CB}= -200 V , I_E=0			-0.25	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-20 mA, I_B= -2mA			-0.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-20 mA, I_B= -2mA			-0.9	
DC current gain	$h_{FE(1)}$	V_{CE}= -10V, I_C= -1mA	60			
	$h_{FE(2)}$	V_{CE}= -10V, I_C= -10mA	80		250	
	$h_{FE(3)}$	V_{CE}= -10V, I_C= -80mA	60			
Transition frequency	f_T	V_{CE}= -20V, I_C= -10mA,f=30MHz	50			MHz

■ Classification of hFE(2)

Rank	A	B	C
Range	80-100	100-200	200-250

PNP Transistors

A92

■ Typical Characterisitics